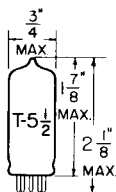


TUNG-SOL

PENTODE

MINIATURE TYPE



GLASS BULB

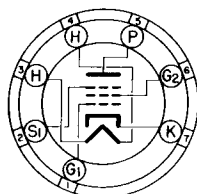
COATED UNIPOTENTIAL CATHODE

HEATER

12.6 VOLTS 150 MA.

AC OR DC

ANY MOUNTING POSITION



BOTTOM VIEW

MINIATURE BUTTON
7 PIN BASE

TCC

THE 12BA6 IS A PENTODE AMPLIFIER HAVING A REMOTE CONTROL GRID CHARACTERISTIC AND UTILIZING THE MINIATURE CONSTRUCTION. AS A RF AMPLIFIER IT IS CHARACTERIZED BY HIGH TRANSCONDUCTANCE AND LOW GRID-PLATE CAPACITANCE.

DIRECT INTERELECTRODE CAPACITANCES

	WITH SHIELD ^A	WITHOUT SHIELD	
GRID TO PLATE: (G ₁ TO P) MAX.	0.0035	0.0035	μuf
INPUT: G ₁ TO (H+K+G ₂ +G ₃ +S)	5.5	5.5	μuf
OUTPUT: P TO (H+K+G ₂ +G ₃ +S)	5.5	5	μuf

^A EXTERNAL SHIELD #316 CONNECTED TO PIN 7.

RATINGS

INTERPRETED ACCORDING TO RMA STANDARD MB-210

HEATER VOLTAGE	12.6	VOLTS
MAXIMUM HEATER-CATHODE VOLTAGE	90	VOLTS
MAXIMUM PLATE VOLTAGE	300	VOLTS
MAXIMUM GRID #2 VOLTAGE	125	VOLTS
MAXIMUM GRID #2 SUPPLY VOLTAGE	300	VOLTS
MAXIMUM NEGATIVE DC GRID #1 VOLTAGE	50	VOLTS
MAXIMUM POSITIVE DC GRID #1 VOLTAGE	0	VOLTS
MAXIMUM PLATE DISSIPATION	3	WATTS
MAXIMUM GRID #2 DISSIPATION	0.6	WATT

TYPICAL OPERATING CONDITIONS AND CHARACTERISTICS

CLASS A₁ AMPLIFIER

HEATER VOLTAGE	12.6	12.6	VOLTS
HEATER CURRENT	150	150	MA.
PLATE VOLTAGE	100	250	VOLTS
GRID #3 VOLTAGE	0	0	VOLTS
GRID #2 VOLTAGE	100	100	VOLTS
CATHODE BIAS RESISTOR	68	68	OHMS
PLATE RESISTANCE (APPROX.)	0.25	1	MEGOHM
TRANSCONDUCTANCE	4 300	4 400	μMHOS
PLATE CURRENT	10.8	11	MA.
GRID #2 CURRENT	4.4	4.2	MA.
GRID #1 VOLTAGE (APPROX. FOR G _m = 40 μMHOS)	-20	-20	VOLTS

12BA6 (6BA6)

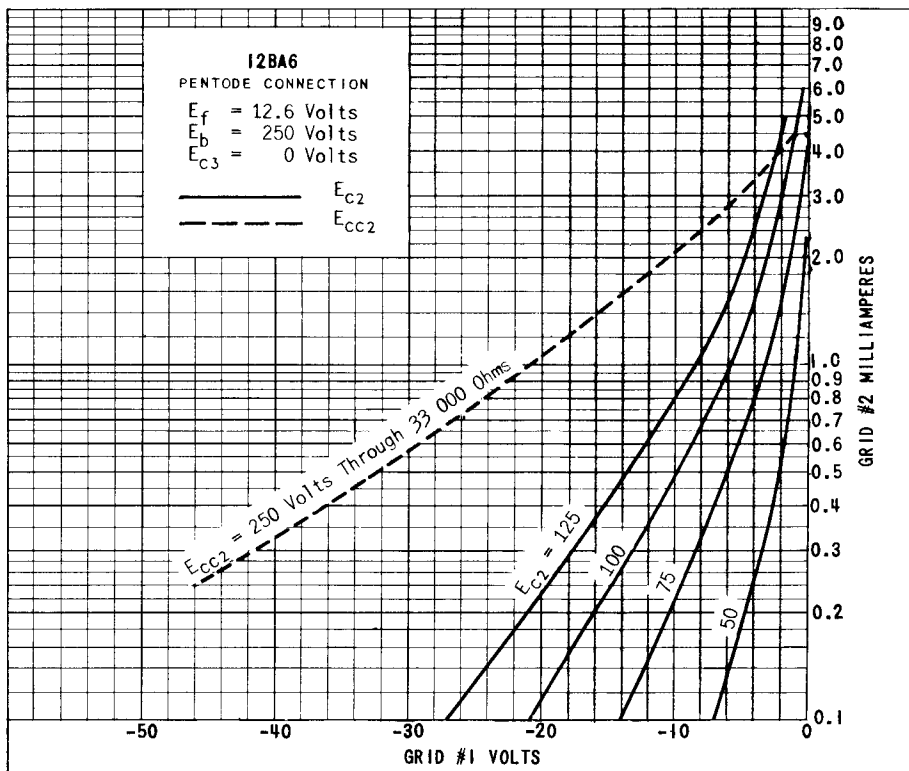
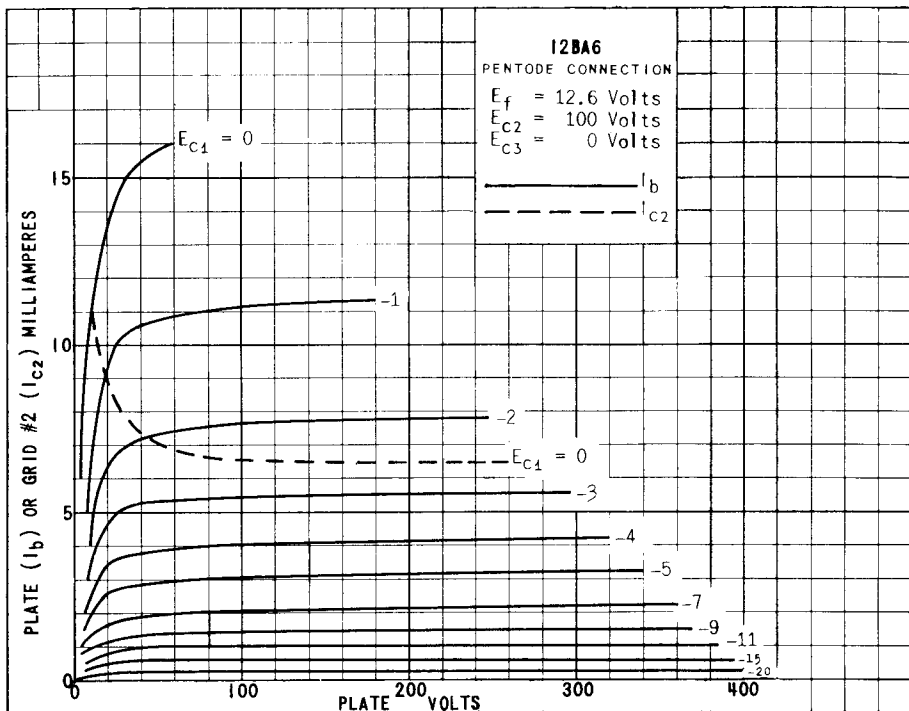
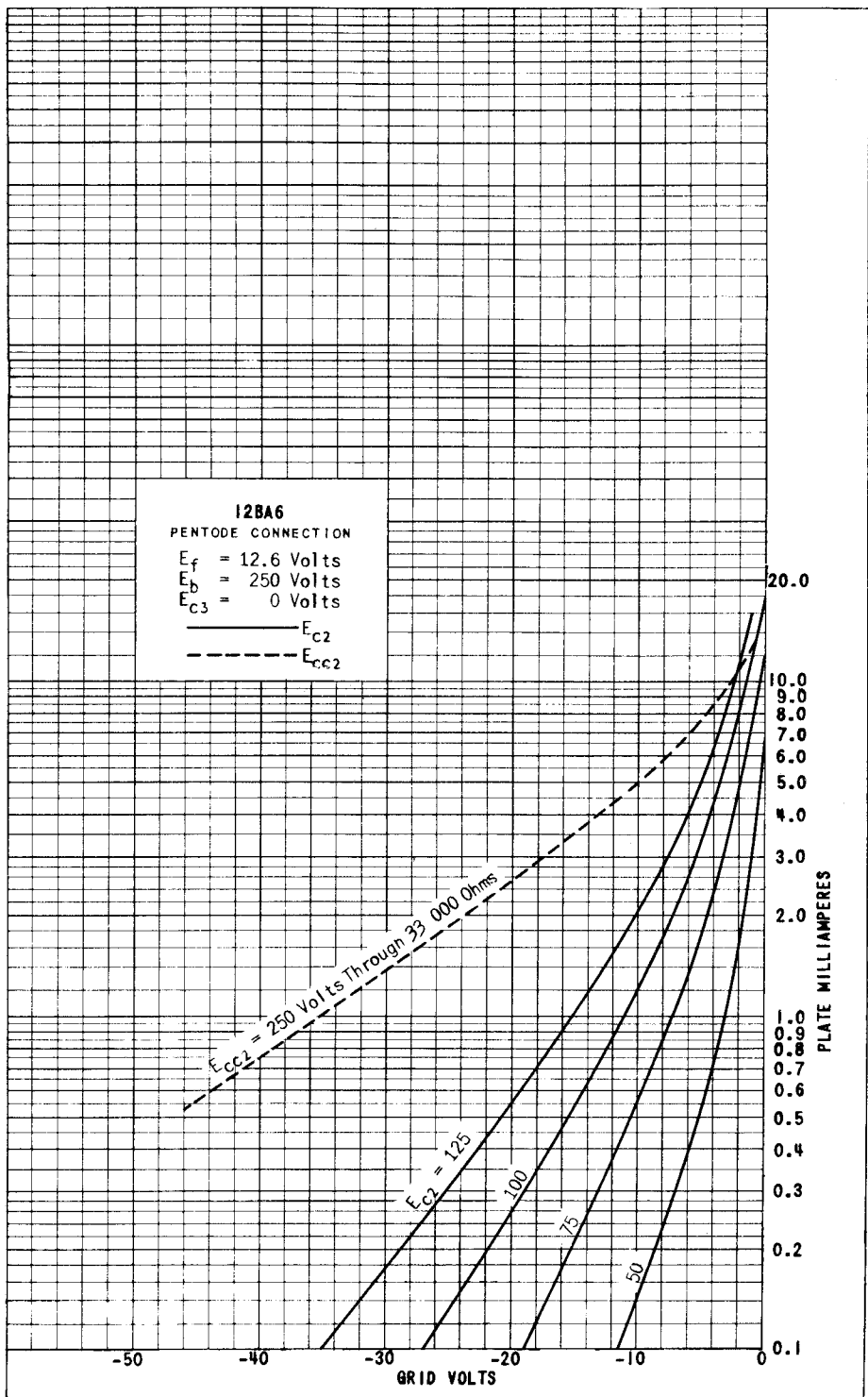
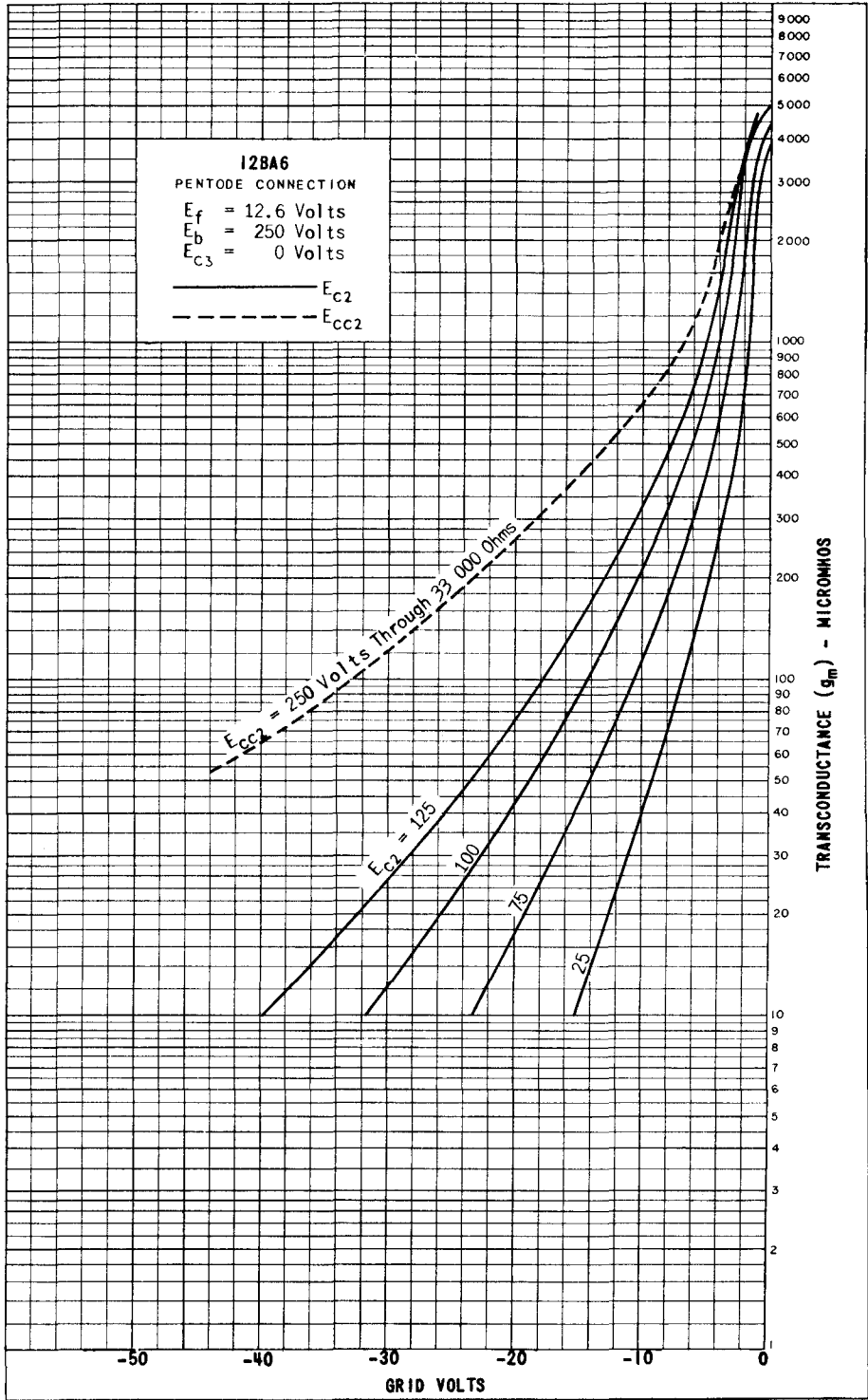


PLATE
1805
MAY 1
1947





TUNG-SOL

PENTODE
MINIATURE TYPE

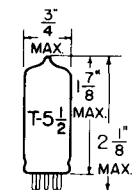
COATED UNIPOTENTIAL CATHODE

HEATER

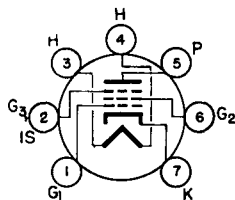
12.6±1.3 VOLTS 0.15 AMP.

AC OR DC

ANY MOUNTING POSITION



GLASS BULB
MINIATURE PENTODE
7 PIN BASE E7-1
OUTLINE DRAWING:
JEDEC 5-9



BOTTOM VIEW
PINNING DIAGRAM
JEDEC 7PK ←

THE 12BA6 IS A PENTODE AMPLIFIER HAVING REMOTE CONTROL GRID CHARACTERISTIC AND UTILIZING THE MINIATURE CONSTRUCTION. AS AN RF AMPLIFIER IT IS CHARACTERIZED BY HIGH TRANSCONDUCTANCE AND LOW GRID-PLATE CAPACITANCE.

DIRECT INTERELECTRODE CAPACITANCES

	WITH SHIELD ^A	WITHOUT SHIELD	
GRID TO PLATE: G_1 TO P (MAX.)	0.0035	0.0035	μf
INPUT: G_1 TO (H+K+ G_2 + G_3 +1S)	5.5	5.5	μf
OUTPUT: P TO (H+K+ G_2 + G_3 +1S)	5.5	5	μf

^A EXTERNAL SHIELD #316 CONNECTED TO PIN #7.

RATINGS

INTERPRETED ACCORDING TO DESIGN CENTER SYSTEM

MAXIMUM PEAK HEATER-CATHODE VOLTAGE:		
HEATER NEGATIVE WITH RESPECT TO CATHODE	200	VOLTS
HEATER POSITIVE WITH RESPECT TO CATHODE	200 ^C	VOLTS
MAXIMUM PLATE VOLTAGE	330	VOLTS
MAXIMUM GRID #2 SUPPLY VOLTAGE	330	VOLTS
MAXIMUM GRID #2 VOLTAGE	SEE J5-C4	
MAXIMUM GRID #3 VOLTAGE	PIN #2 CONNECTED TO PIN #7 AT SOCKET	
MAXIMUM POSITIVE DC GRID #1 VOLTAGE	0	VOLTS
MAXIMUM NEGATIVE DC GRID #1 VOLTAGE	-55	VOLTS
MAXIMUM PLATE DISSIPATION	3.4	WATTS
MAXIMUM GRID #2 DISSIPATION:		
FOR VOLTAGES UP TO 165 VOLTS	0.7	WATT
FOR VOLTAGES BETWEEN 165 & 330 VOLTS	SEE J5-C4	

^C THE DC COMPONENT MUST NOT EXCEED 100 VOLTS.

TYPICAL OPERATING CONDITIONS AND CHARACTERISTICS

CLASS A₁ AMPLIFIER

PLATE VOLTAGE	100	250	VOLTS
GRID #3 VOLTAGE	0	0	VOLTS
GRID #2 VOLTAGE	100	100	VOLTS
CATHODE BIAS RESISTOR	68	68	OHMS
PLATE RESISTANCE (APPROX.)	0.25	1.0	MEG OHM
TRANSCONDUCTANCE	4 300	4 400	μMHOS
PLATE CURRENT	10.8	11	MA.
GRID #2 CURRENT	4.4	4.2	MA.
GRID #1 VOLTAGE (APPROX.) FOR $G_m = 40 \mu\text{MHOS}$	-20	-20	VOLTS

→ INDICATES A CHANGE.

12BA6

